YJ Planar Schottky Barrier Diode Die Specification

150V 20A, 108mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB108H150AS-280A

Main Products Characterstics

- Average forward current: IF(AV) = 20 A
- Maximum operating junction temperature: Tj = 175 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

I_F = 20 A

Pulse Test: tp = 300 μs, δ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area

Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.